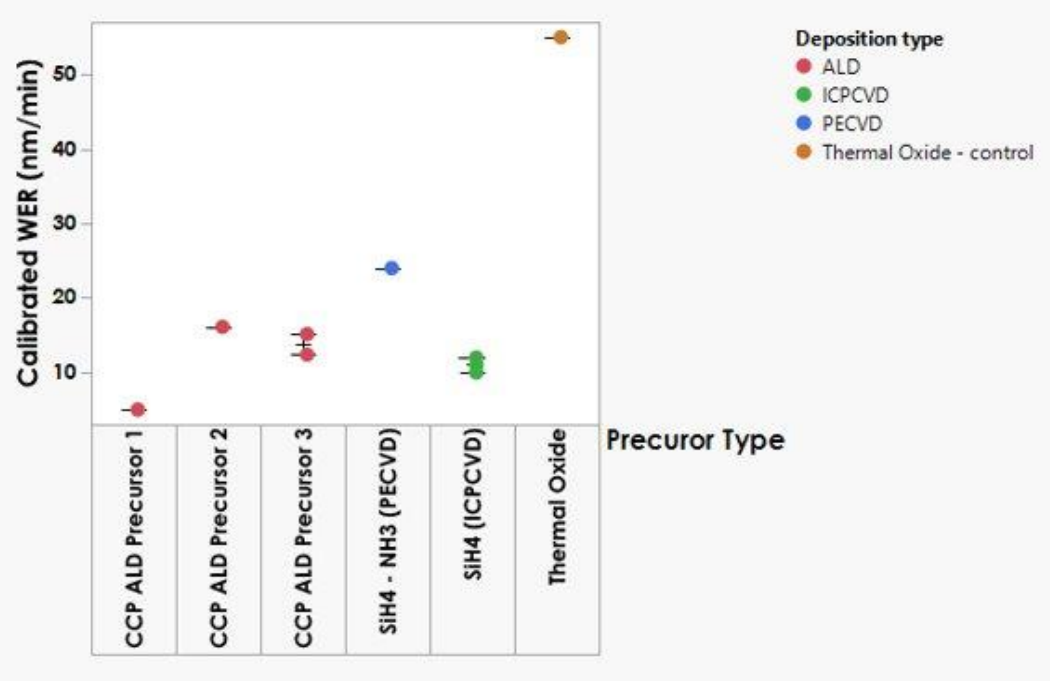

Figure 1: Lowest WER for SiNx (< 5 nm/min) deposited with CCP plasma and precursor 1

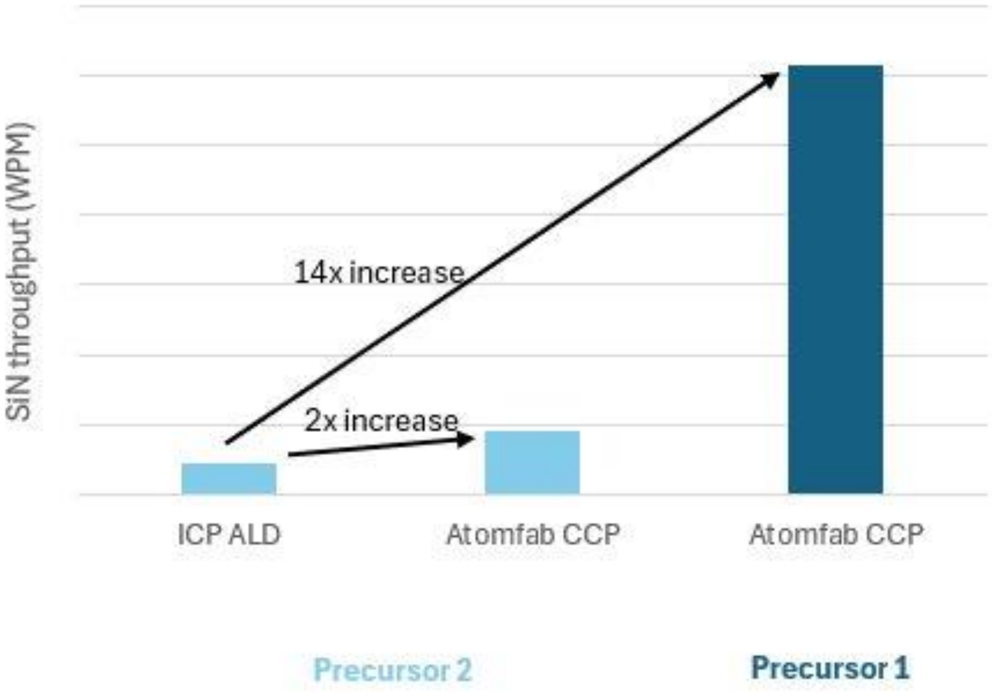

Figure 2: 14x SiN throughput with Oxford Instruments Atomfab CCP ALD System compared to ICP ALD systems

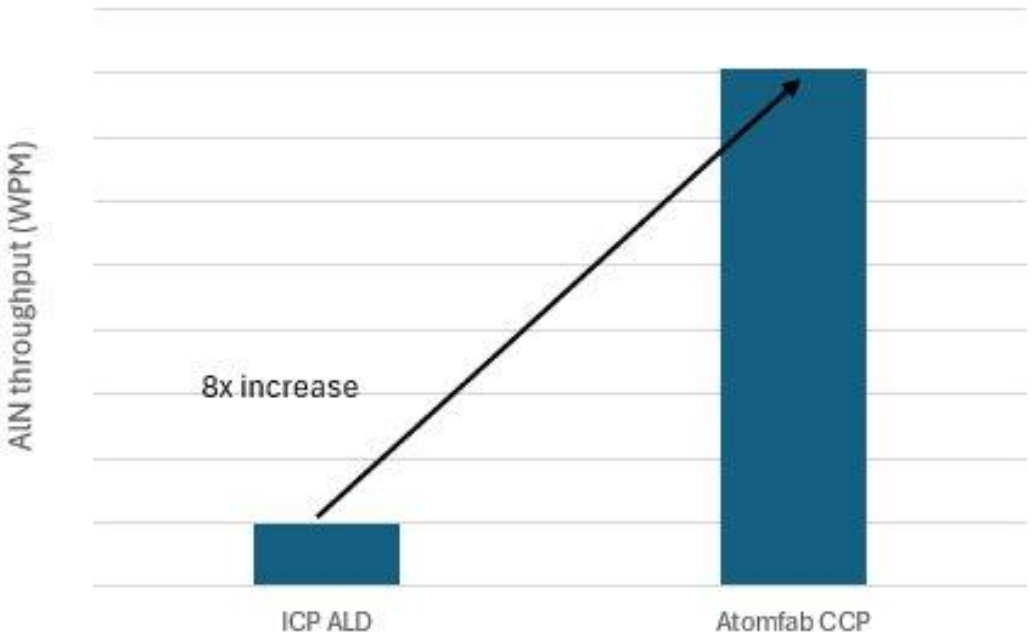

Figure 3: 8x AlN throughput with Oxford Instruments Atomfab CCP ALD System compared to ICP ALD systems